MPS2907A

Preferred Device

General Purpose Transistors

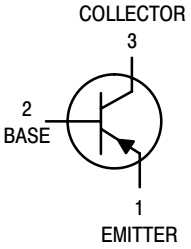
PNP Silicon

ON Semiconductor®

http://onsemi.com

Features

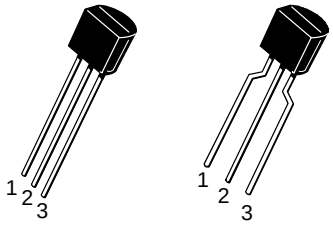
- Pb−Free Packages are Available*



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	−60	Vdc
Collector−Base Voltage	V_{CBO}	−60	Vdc
Emitter−Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

TO−92
CASE 29
STYLE 1

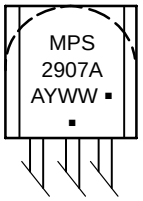


THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (Note 1) (I_C = −10 mAdc, I_B = 0)		$V_{(BR)CEO}$	−60	−	Vdc
Collector−Base Breakdown Voltage (I_C = −10 μAdc, I_E = 0)		$V_{(BR)CBO}$	−60	−	Vdc
Emitter−Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)		$V_{(BR)EBO}$	−5.0	−	Vdc
Collector Cutoff Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)		I_{CEX}	−	−50	nAdc
Collector Cutoff Current (V_{CB} = −50 Vdc, I_E = 0) (V_{CB} = −50 Vdc, I_E = 0, T_A = 150°C)		I_{CBO}	 − −	 −0.01 −10	μAdc
Base Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)		I_B	−	−50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = −0.1 mAdc, V_{CE} = −10 Vdc) (I_C = −1.0 mAdc, V_{CE} = −10 Vdc) (I_C = −10 mAdc, V_{CE} = −10 Vdc) (I_C = −150 mAdc, V_{CE} = −10 Vdc) (Note 1) (I_C = −500 mAdc, V_{CE} = −10 Vdc) (Note 1)		h_{FE}	 75 100 100 100 50	 − − − 300 −	−
Collector−Emitter Saturation Voltage (Note 1) (I_C = −150 mAdc, I_B = −15 mAdc) (I_C = −500 mAdc, I_B = −50 mAdc)		$V_{CE(sat)}$	 − −	 −0.4 −1.6	Vdc
Base−Emitter Saturation Voltage (Note 1) (I_C = −150 mAdc, I_B = −15 mAdc) (I_C = −500 mAdc, I_B = −50 mAdc)		$V_{BE(sat)}$	 − −	 −1.3 −2.6	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (Notes 1 and 2), (I_C = −50 mAdc, V_{CE} = −20 Vdc, f = 100 MHz)		f_T	200	−	MHz
Output Capacitance (V_{CB} = −10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	−	8.0	pF
Input Capacitance (V_{EB} = −2.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	−	30	pF
SWITCHING CHARACTERISTICS					
Turn−On Time	(V_{CC} = −30 Vdc, I_C = −150 mAdc, I_{B1} = −15 mAdc) (Figures 1 and 5)	t_{on}	−	45	ns
Delay Time		t_d	−	10	ns
Rise Time		t_r	−	40	ns
Turn−Off Time	(V_{CC} = −6.0 Vdc, I_C = −150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_{off}	−	100	ns
Storage Time		t_s	−	80	ns
Fall Time		t_f	−	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

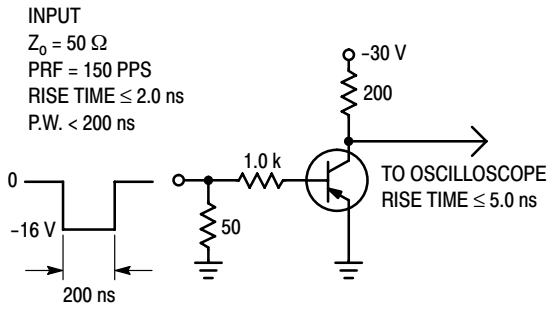


Figure 1. Delay and Rise Time Test Circuit

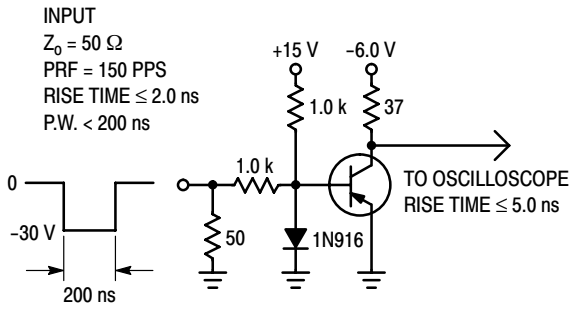


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

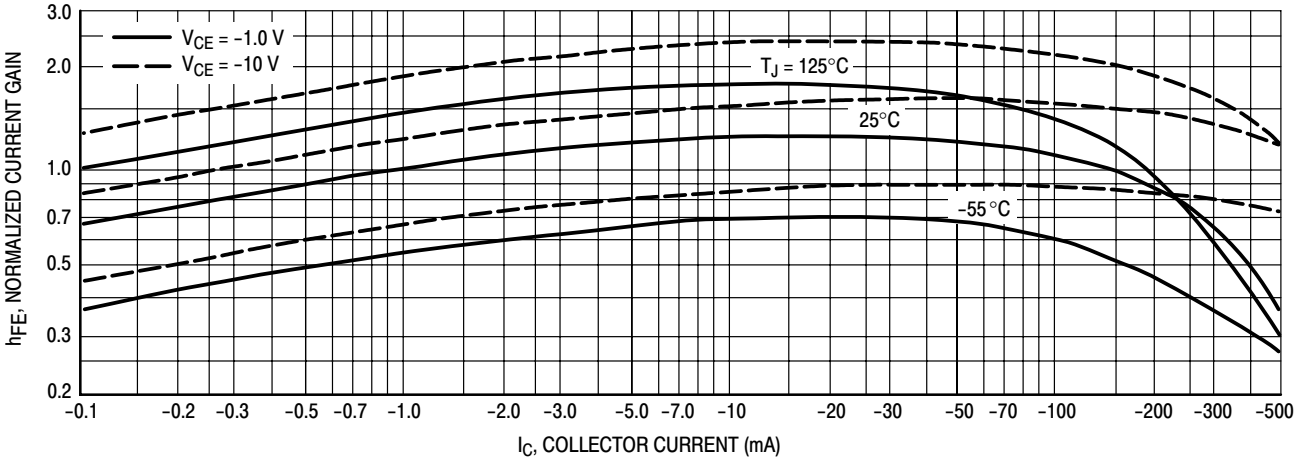


Figure 3. DC Current Gain

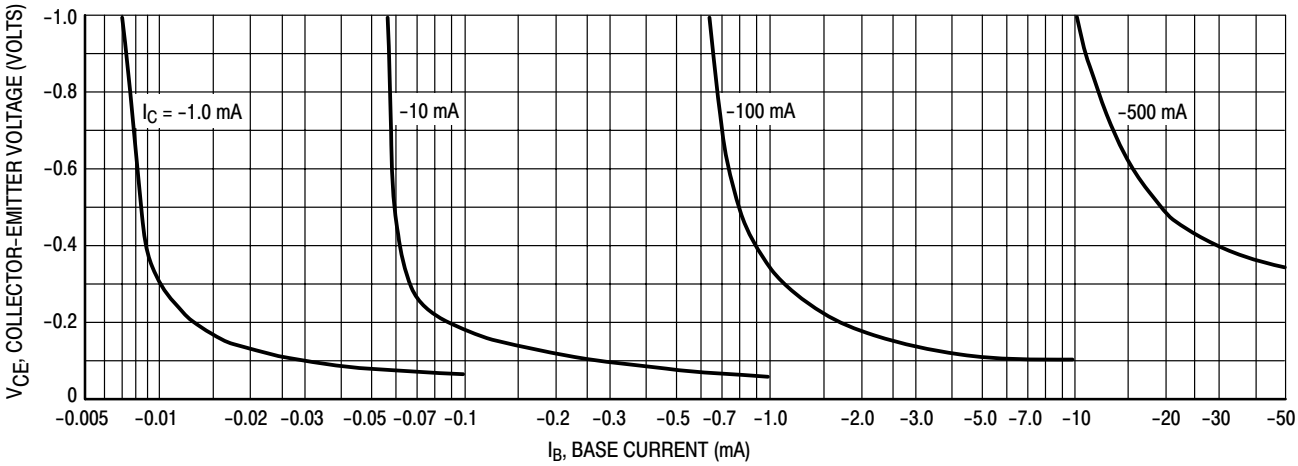


Figure 4. Collector Saturation Region

ORDERING INFORMATION

Device	Package	Shipping†
MPS2907A	TO−92	5000 Units / Bulk
MPS2907AG	TO−92 (Pb−Free)	
MPS2907ARLG	TO−92 (Pb−Free)	2000 / Tape & Reel
MPS2907ARLRA	TO−92	
MPS2907ARLRAG	TO−92 (Pb−Free)	
MPS2907ARLRPG	TO−92 (Pb−Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

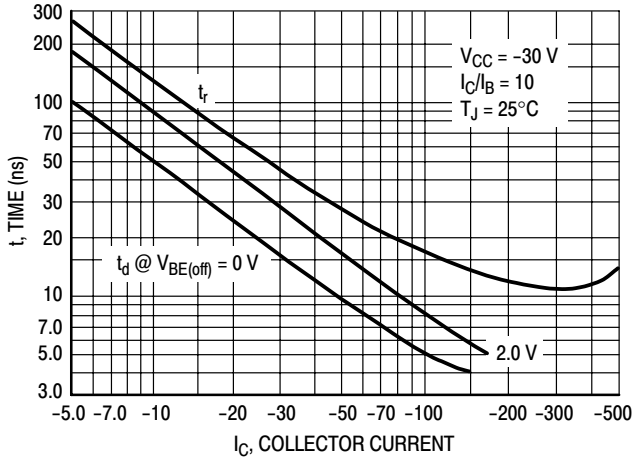


Figure 5. Turn−On Time

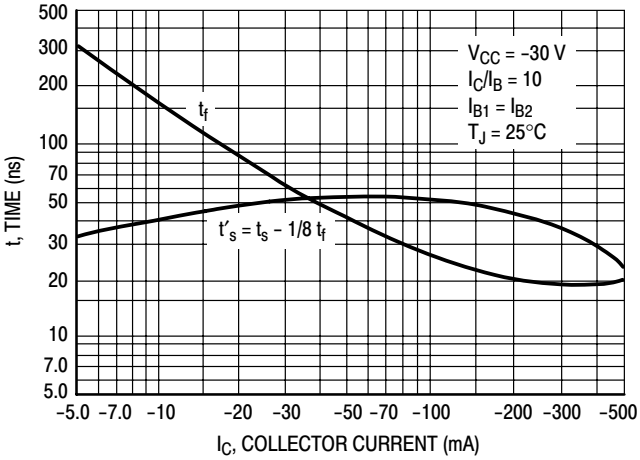


Figure 6. Turn−Off Time

TYPICAL SMALL−SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

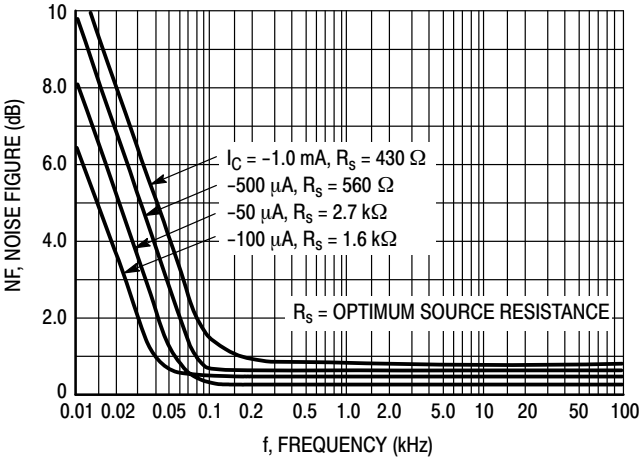


Figure 7. Frequency Effects

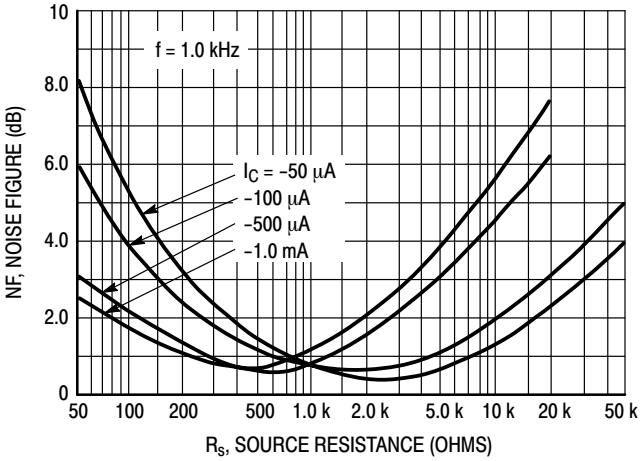


Figure 8. Source Resistance Effects

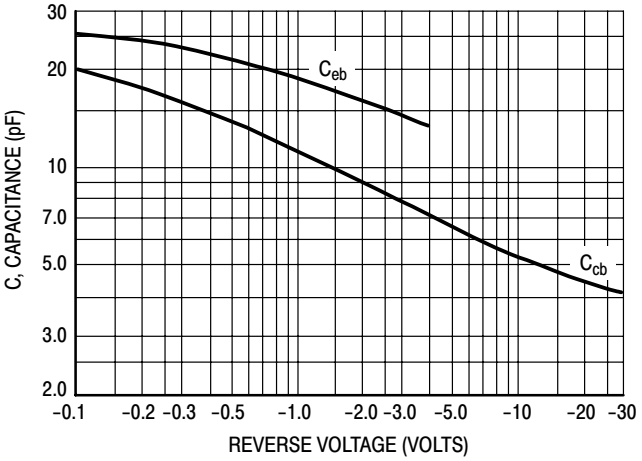


Figure 9. Capacitances

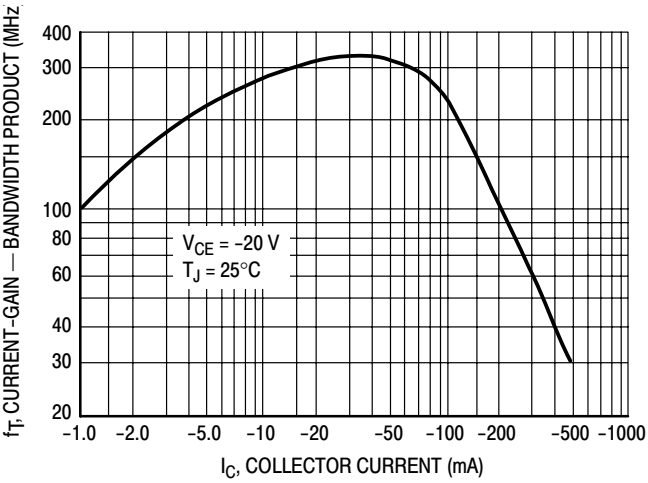


Figure 10. Current−Gain — Bandwidth Product

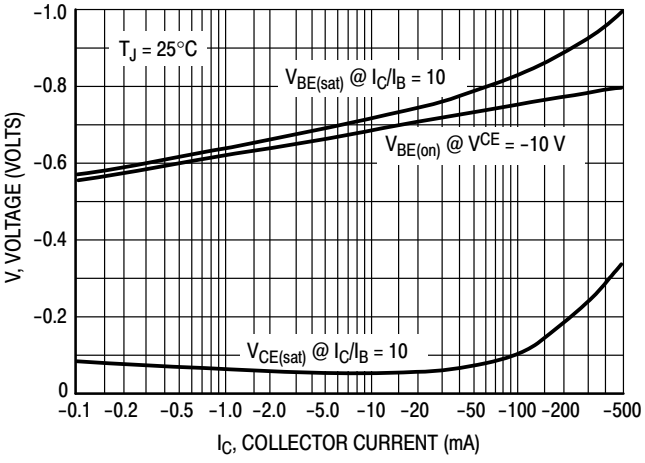


Figure 11. “On” Voltage

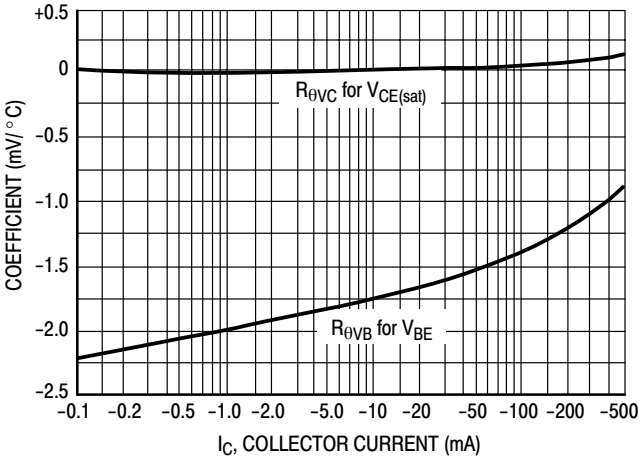
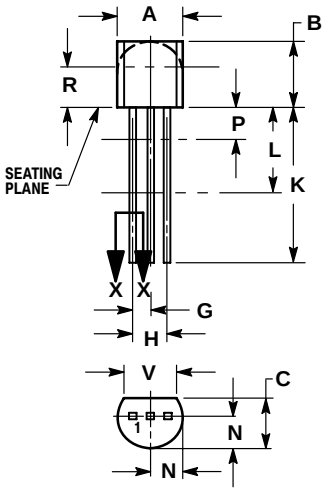


Figure 12. Temperature Coefficients

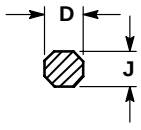
MPS2907A

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−11
ISSUE AM



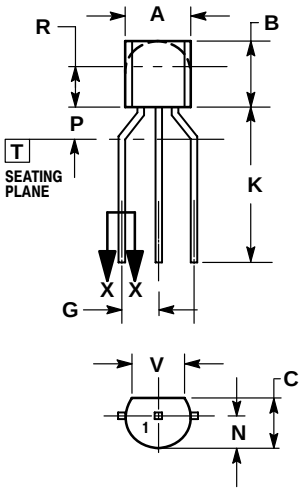
STRAIGHT LEAD
BULK PACK



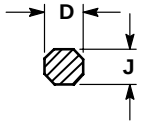
SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS	
DIM	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
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Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

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